

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _A = +25°C
-30V	75mΩ @ V _{GS} = -10V	-3.9A
	98mΩ @ V _{GS} = -4.5V	-3.3A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

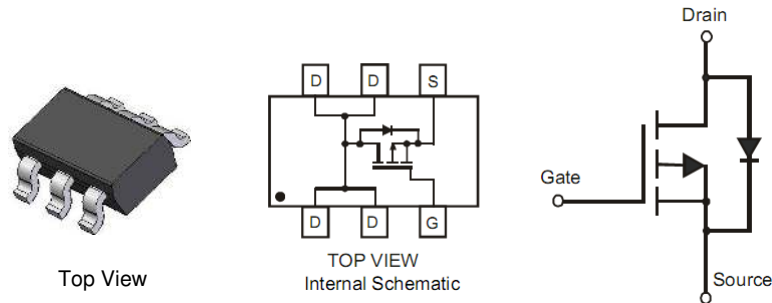
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting
- Motor Control

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013 grams (Approximate)

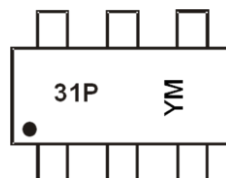


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3105LVT-7	TSOT26	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



31P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-3.1	A
		T _A = +70°C		-2.5	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-2.7	A
		T _A = +70°C		-2.2	
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-3.9	A
		T _A = +70°C		-3.1	
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-3.3	A
		T _A = +70°C		-2.7	
Maximum Continuous Body Diode Forward Current			I _S	-2.2	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.15	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	108	°C/W
Total Power Dissipation (Note 6)	P _D	1.75	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	72	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	23.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-100	nA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-0.9	-1.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	65	75	mΩ	V _{GS} = -10V, I _D = -4.2A
		—	75	98		V _{GS} = -4.5V, I _D = -4.0A
		—	98	150		V _{GS} = -2.5V, I _D = -3.0A
Forward Transfer Admittance	Y _{fs}	—	5	—	S	V _{DS} = -15V, I _D = -4.0A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	839	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	47	—		
Reverse Transfer Capacitance	C _{rss}	—	43	—		
Gate Resistance	R _G	—	12.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	9.0	—	nC	V _{DS} = -15V, I _D = -4.0A
Total Gate Charge (V _{GS} = -10.0V)	Q _g	—	19.8	—		
Gate-Source Charge	Q _{gs}	—	1.6	—		
Gate-Drain Charge	Q _{gd}	—	1.1	—		
Turn-On Delay Time	t _{D(ON)}	—	9.7	—	ns	V _{GS} = -10V, V _{DD} = -15V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	17.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	269	—		
Turn-Off Fall Time	t _F	—	64	—		

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

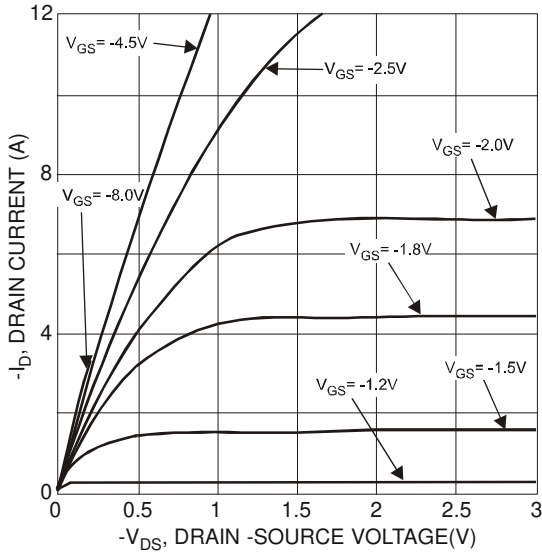


Fig. 1 Typical Output Characteristics

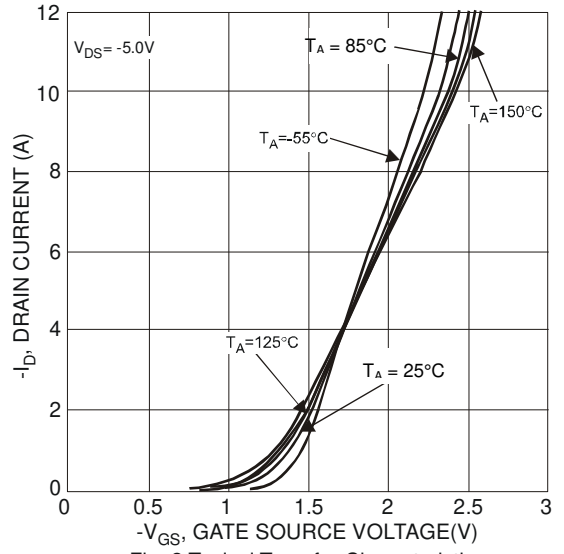


Fig. 2 Typical Transfer Characteristics

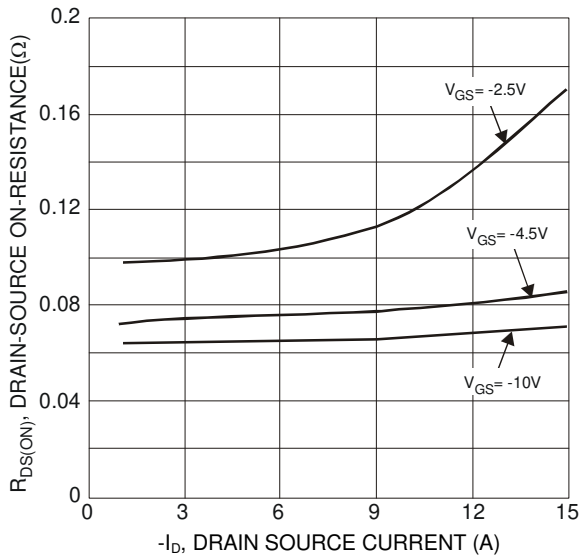


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

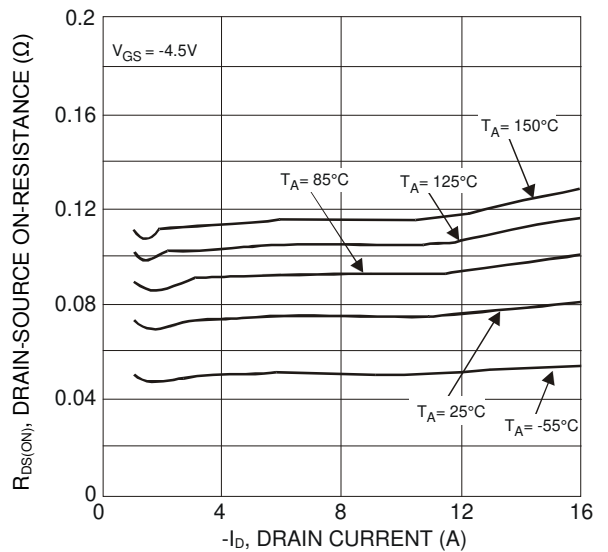


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

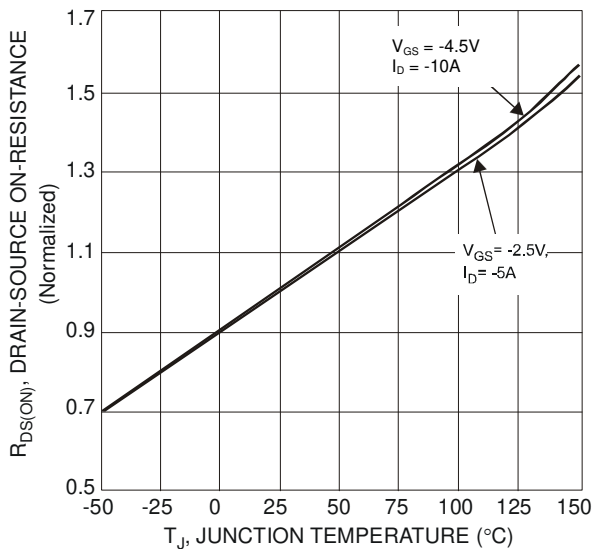


Fig. 5 On-Resistance Variation with Temperature

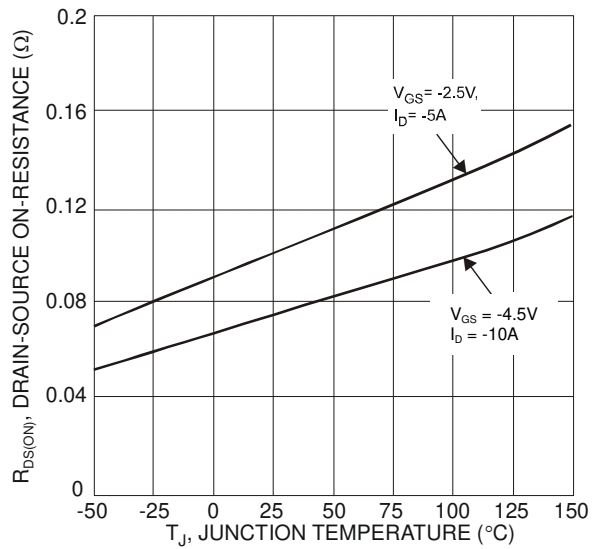


Fig. 6 On-Resistance Variation with Temperature

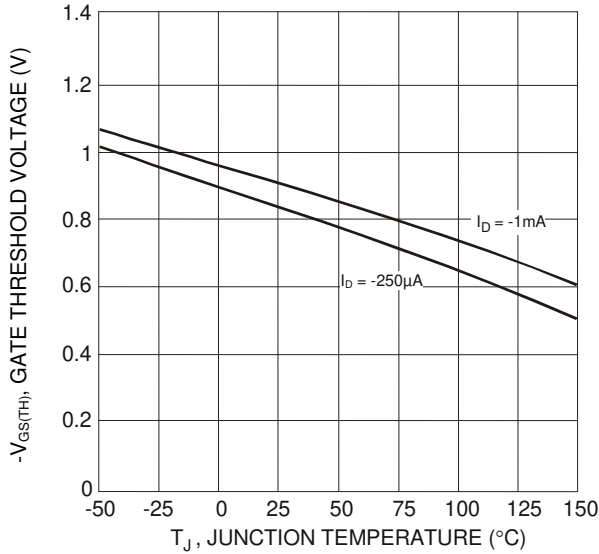


Fig. 7 Gate Threshold Variation vs. Junction Temperature

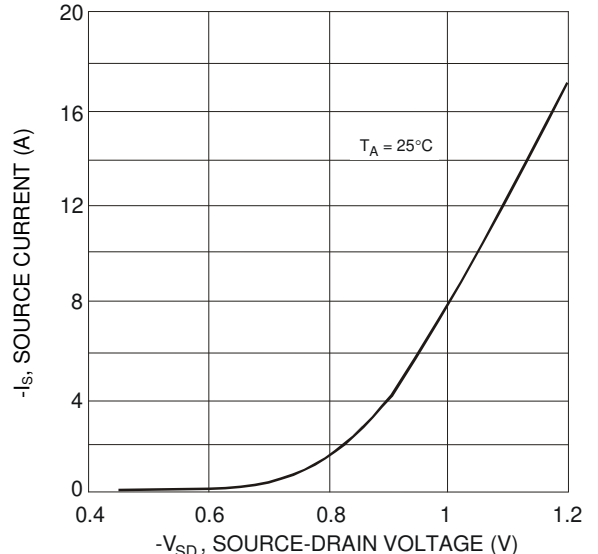


Fig. 8 Diode Forward Voltage vs. Current

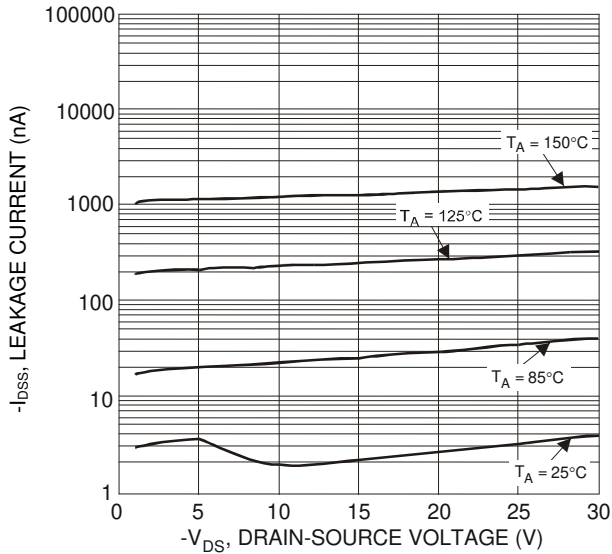


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

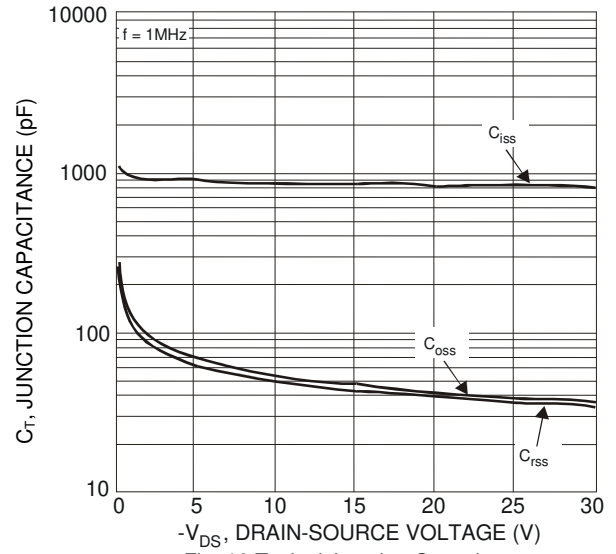


Fig. 10 Typical Junction Capacitance

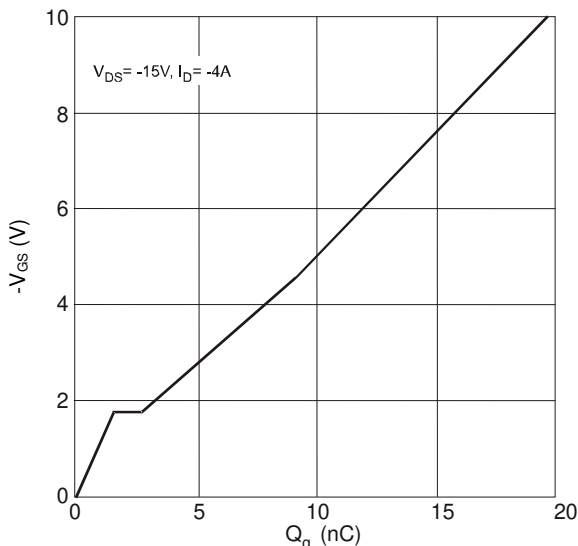


Fig. 11 Gate Charge Characteristics

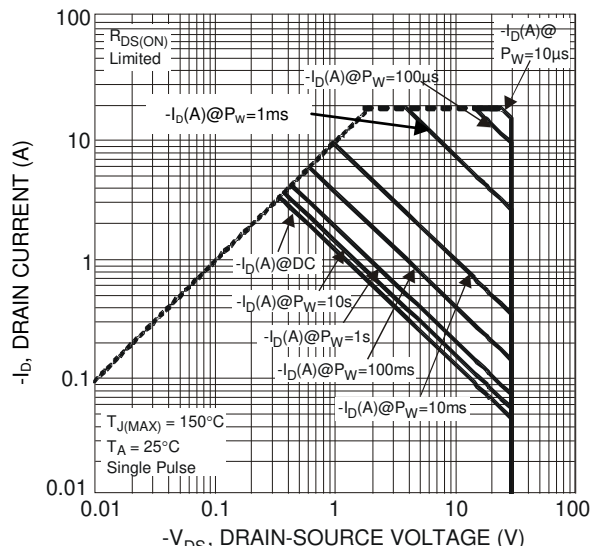


Fig. 12 SOA, Safe Operation Area

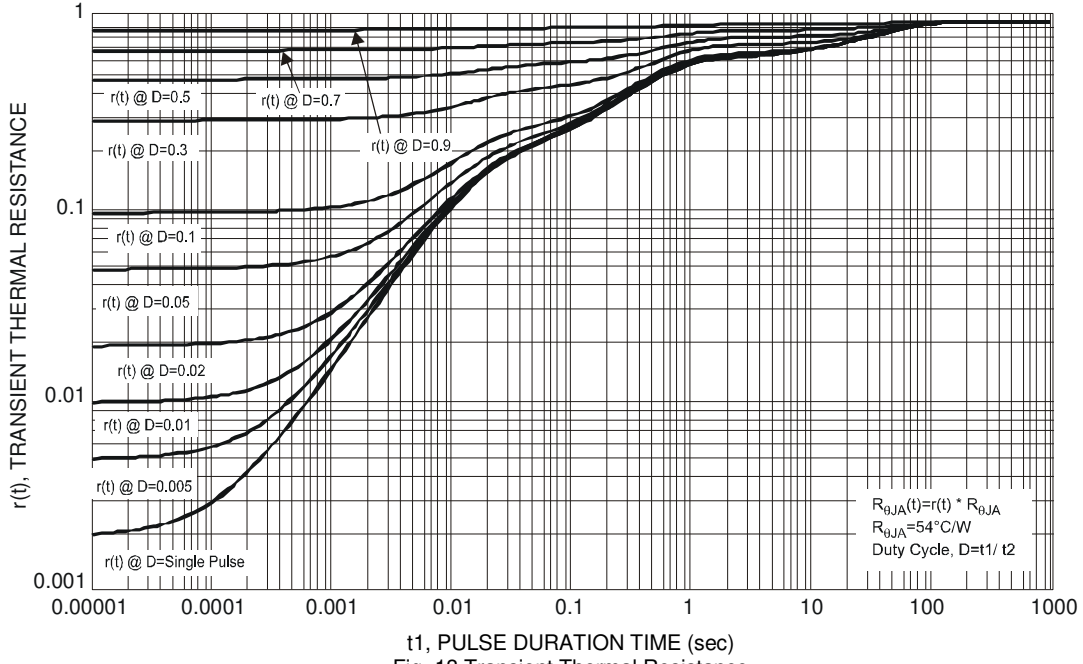
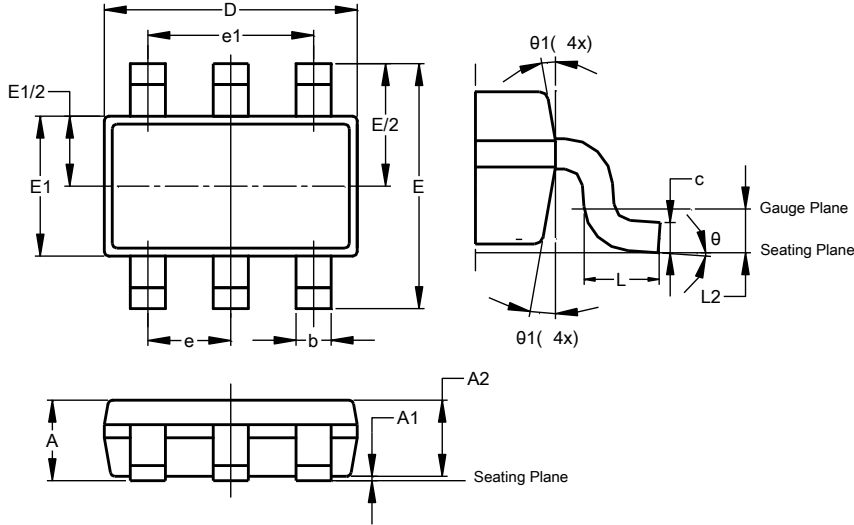


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

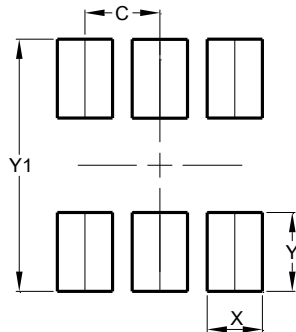


TSOT26			
Dim	Min	Max	Typ
A	-	1.00	-
A1	0.010	0.100	-
A2	0.840	0.900	-
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	-
c	0.120	0.200	-
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	-
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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